

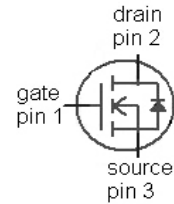
## OptiMOS<sup>®</sup> 2 Power-Transistor

### Features

- Ideal for high-frequency dc/dc converters
- Qualified according to JEDEC<sup>1)</sup> for target applications
- N-channel, logic level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Superior thermal resistance
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant

### Product Summary

|                  |     |            |
|------------------|-----|------------|
| $V_{DS}$         | 30  | V          |
| $R_{DS(on),max}$ | 4.1 | m $\Omega$ |
| $I_D$            | 50  | A          |



| Type           | IPD04N03LB G  | IPS04N03LB G  | IPF04N03LB G  | IPU04N03LB G |
|----------------|---------------|---------------|---------------|--------------|
|                |               |               |               |              |
| <b>Package</b> | PG-TO252-3-11 | PG-TO251-3-11 | PG-TO252-3-23 | PG-TO251-3-1 |
| <b>Marking</b> | 04N03LB       | 04N03LB       | 04N03LB       | 04N03LB      |

Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol            | Conditions  | Value       | Unit              |
|-------------------------------------|-------------------|---|-------------|-------------------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}^{2)}$   | 50          | A                 |
|                                     |                   | $T_C=100\text{ °C}$   | 50          |                   |
| Pulsed drain current                | $I_{D,pulse}$     | $T_C=25\text{ °C}^{3)}$   | 200         |                   |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=50\text{ A}$ , $R_{GS}=25\ \Omega$   | 430         | mJ                |
| Reverse diode $dv/dt$               | $dv/dt$           | $I_D=50\text{ A}$ , $V_{DS}=20\text{ V}$ ,<br>$di/dt=200\text{ A}/\mu\text{s}$ ,<br>$T_{j,max}=175\text{ °C}$ | 6           | kV/ $\mu\text{s}$ |
| Gate source voltage <sup>4)</sup>   | $V_{GS}$          |   | $\pm 20$    | V                 |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$  | 115         | W                 |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |   | -55 ... 175 | °C                |
| IEC climatic category; DIN IEC 68-1 |                   |   | 55/175/56   |                   |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

**Thermal characteristics**

|                                     |            |  |   |   |     |     |
|-------------------------------------|------------|--|---|---|-----|-----|
| Thermal resistance, junction - case | $R_{thJC}$ |  | - | - | 1.3 | K/W |
| SMD version, device on PCB          | $R_{thJA}$ | minimal footprint                            | - | - | 75  |     |
|                                     |            | 6 cm <sup>2</sup> cooling area <sup>5)</sup> | - | - | 50  |     |

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**
**Static characteristics**

|                                  |               |  |     |     |     |               |
|----------------------------------|---------------|--|-----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                       | 30  | -   | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=70\text{ }\mu\text{A}$                 | 1.2 | 1.6 | 2   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$  | -   | 0.1 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=30\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$ | -   | 10  | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                    | -   | 10  | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=4.5\text{ V}, I_D=50\text{ A}$                     | -   | 4.9 | 6.0 | m $\Omega$    |
|                                  |               | $V_{GS}=4.5\text{ V}, I_D=50\text{ A},$<br>SMD version     | -   | 4.7 | 5.8 |               |
|                                  |               | $V_{GS}=10\text{ V}, I_D=50\text{ A}$                      | -   | 3.7 | 4.3 |               |
|                                  |               | $V_{GS}=10\text{ V}, I_D=50\text{ A},$<br>SMD version      | -   | 3.5 | 4.1 |               |
| Gate resistance                  | $R_G$         |  | -   | 1.3 | -   | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max},$<br>$I_D=50\text{ A}$       | 51  | 102 | -   | S             |

<sup>1)</sup> J-STD20 and JESD22

<sup>1)</sup> Current is limited by bondwire; with an  $R_{thJC}=1.3\text{ K/W}$  the chip is able to carry 142 A.

<sup>3)</sup> See figure 3

<sup>4)</sup>  $T_{j,max}=150\text{ °C}$  and duty cycle  $D<0.25$  for  $V_{GS}<-5\text{ V}$ 
<sup>5)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Dynamic characteristics

|                              |              |   |   |      |      |    |
|------------------------------|--------------|---|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=15\text{ V},$<br>$f=1\text{ MHz}$                    | - | 3900 | 5200 | pF |
| Output capacitance           | $C_{oss}$    |   | - | 1400 | 1900 |    |
| Reverse transfer capacitance | $C_{rss}$    |   | - | 180  | 270  |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=15\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=25\text{ A}, R_G=2.7\ \Omega$ | - | 14   | 21   | ns |
| Rise time                    | $t_r$        |   | - | 10   | 14   |    |
| Turn-off delay time          | $t_{d(off)}$ |   | - | 43   | 65   |    |
| Fall time                    | $t_f$        |   | - | 6.0  | 9    |    |

#### Gate Charge Characteristics<sup>6)</sup>

|                              |               |   |   |     |     |    |
|------------------------------|---------------|---|---|-----|-----|----|
| Gate to source charge        | $Q_{gs}$      | $V_{DD}=15\text{ V}, I_D=25\text{ A},$<br>$V_{GS}=0\text{ to }5\text{ V}$ | - | 11  | 15  | nC |
| Gate charge at threshold     | $Q_{g(th)}$   |   | - | 6.3 | 8.3 |    |
| Gate to drain charge         | $Q_{gd}$      |   | - | 7.7 | 11  |    |
| Switching charge             | $Q_{sw}$      |   | - | 13  | 18  |    |
| Gate charge total            | $Q_g$         |   | - | 30  | 40  |    |
| Gate plateau voltage         | $V_{plateau}$ |   | - | 3.1 | -   |    |
| Gate charge total, sync. FET | $Q_{g(sync)}$ | $V_{DS}=0.1\text{ V},$<br>$V_{GS}=0\text{ to }5\text{ V}$                 | - | 27  | 35  | nC |
| Output charge                | $Q_{oss}$     | $V_{DD}=15\text{ V}, V_{GS}=0\text{ V}$                                   | - | 31  | 42  |    |

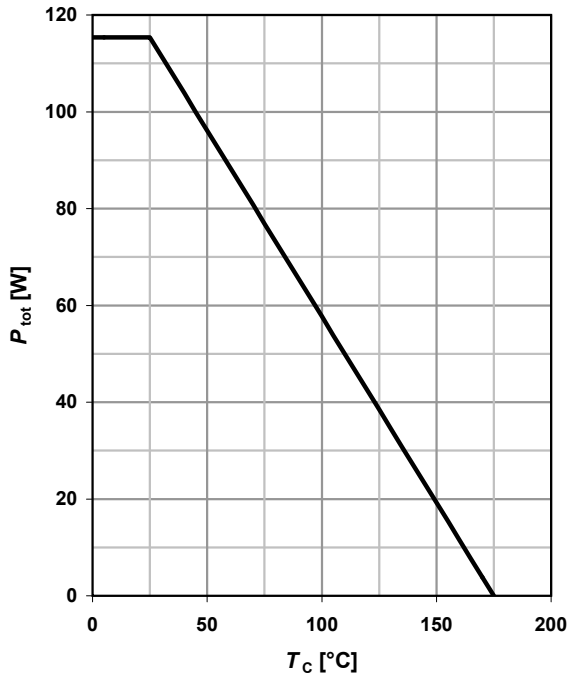
#### Reverse Diode

|                                  |               |   |   |      |     |    |
|----------------------------------|---------------|---|---|------|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ }^\circ\text{C}$  | - | -    | 50  | A  |
| Diode pulse current              | $I_{S,pulse}$ |   | - | -    | 350 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=50\text{ A},$<br>$T_j=25\text{ }^\circ\text{C}$ | - | 0.89 | 1.2 | V  |
| Reverse recovery charge          | $Q_{rr}$      | $V_R=15\text{ V}, I_F=I_S,$<br>$di_F/dt=400\text{ A}/\mu\text{s}$       | - | -    | 10  | nC |

<sup>6)</sup> See figure 16 for gate charge parameter definition

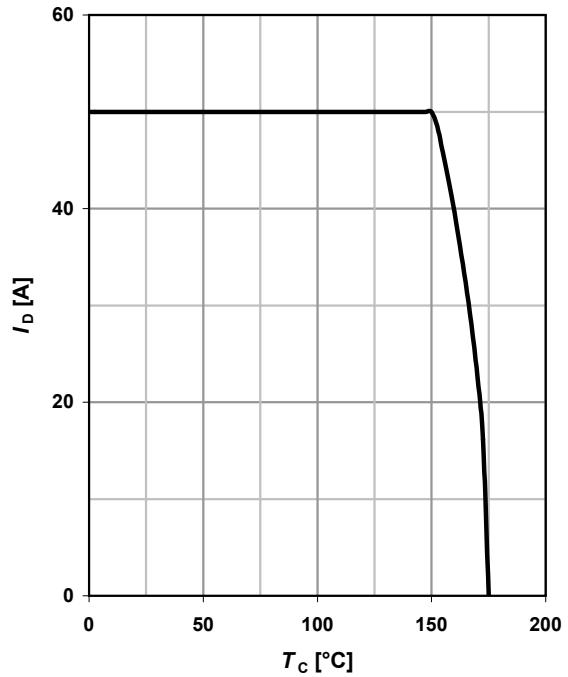
**1 Power dissipation**

$P_{tot}=f(T_C)$



**2 Drain current**

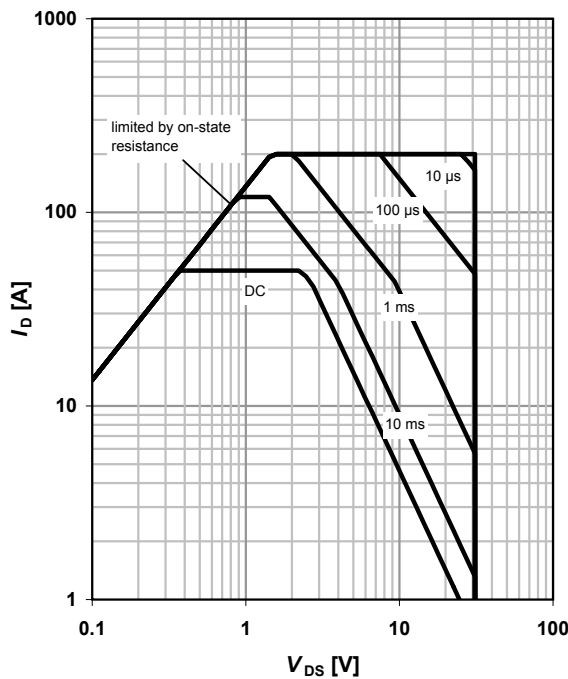
$I_D=f(T_C); V_{GS}\geq 10\text{ V}$



**3 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ °C}; D=0$

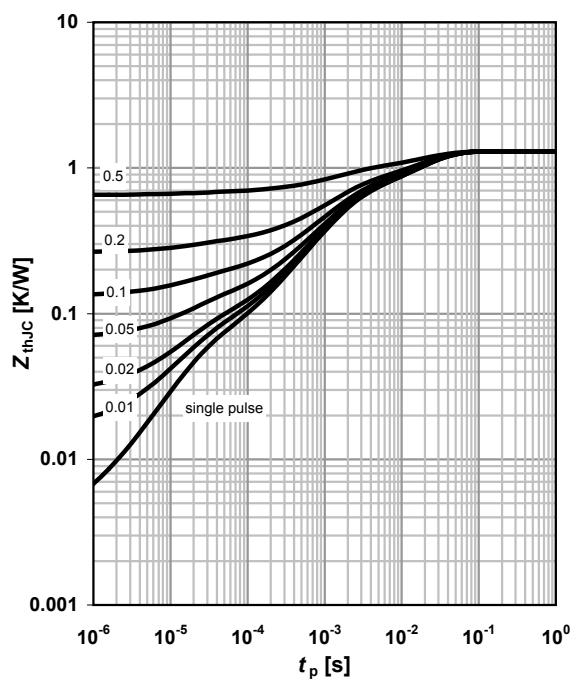
parameter:  $t_p$



**4 Max. transient thermal impedance**

$Z_{thJC}=f(t_p)$

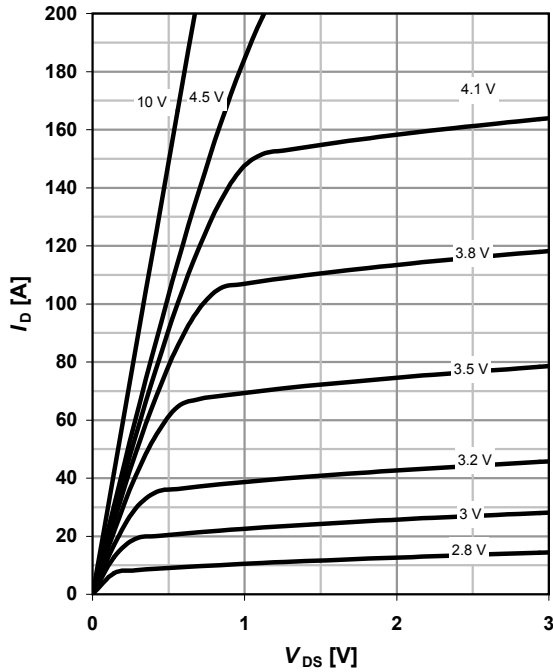
parameter:  $D=t_p/T$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 25\text{ }^\circ\text{C}$

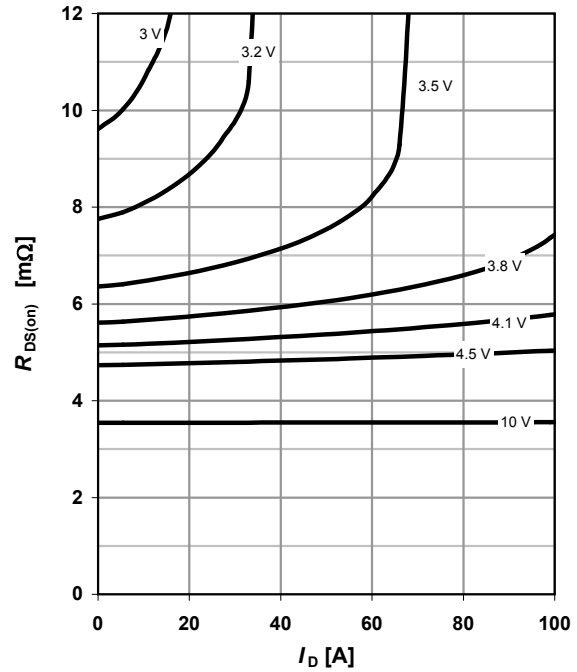
parameter:  $V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D); T_j = 25\text{ }^\circ\text{C}$

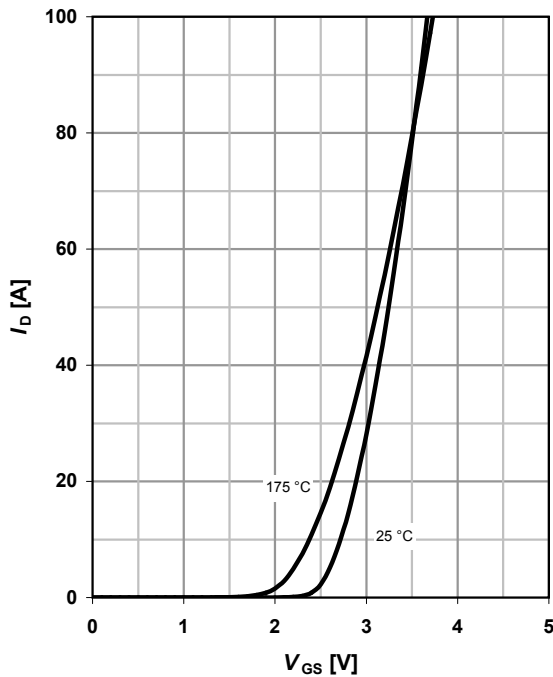
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

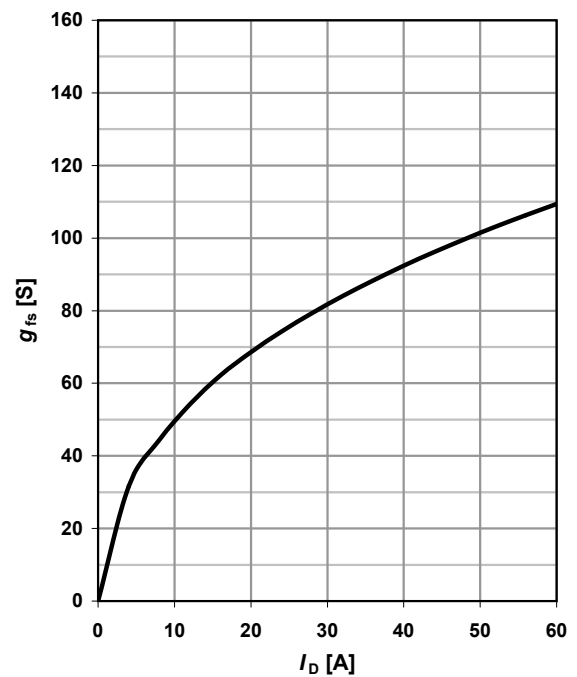
$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

parameter:  $T_j$



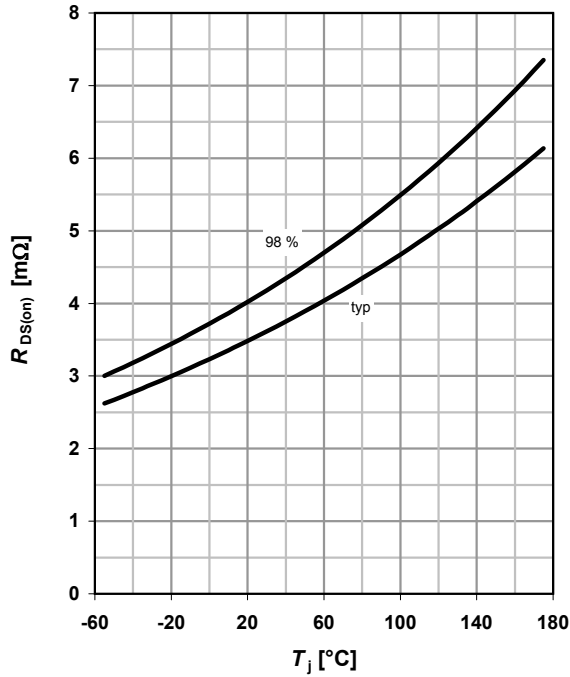
**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25\text{ }^\circ\text{C}$



**9 Drain-source on-state resistance**

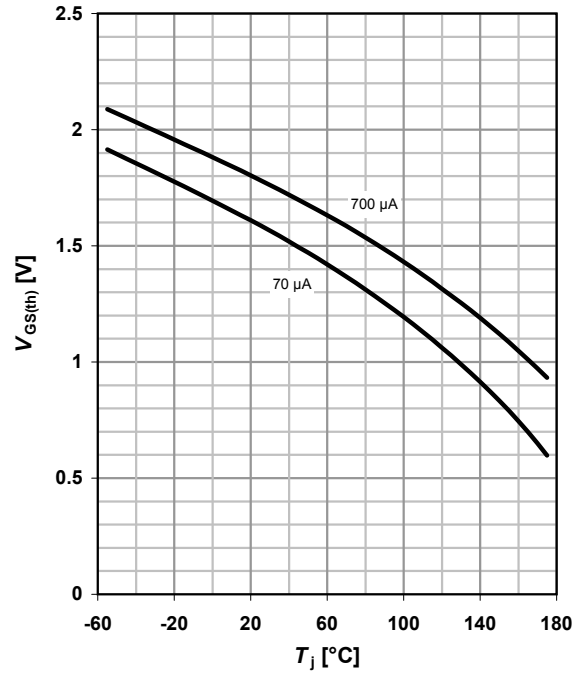
$R_{DS(on)} = f(T_j); I_D = 50 \text{ A}; V_{GS} = 10 \text{ V}$



**10 Typ. gate threshold voltage**

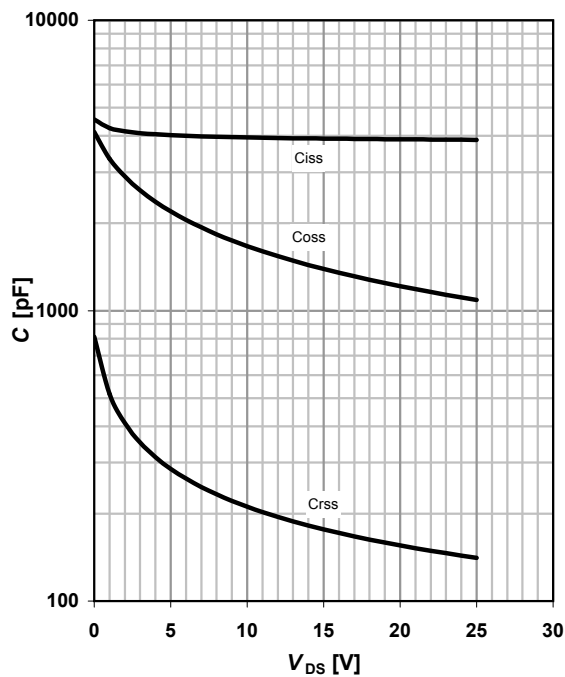
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter:  $I_D$



**11 Typ. capacitances**

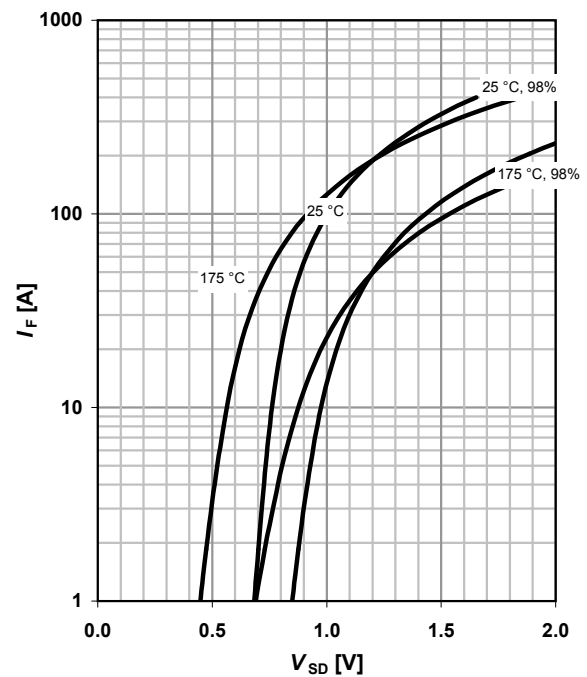
$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$



**12 Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

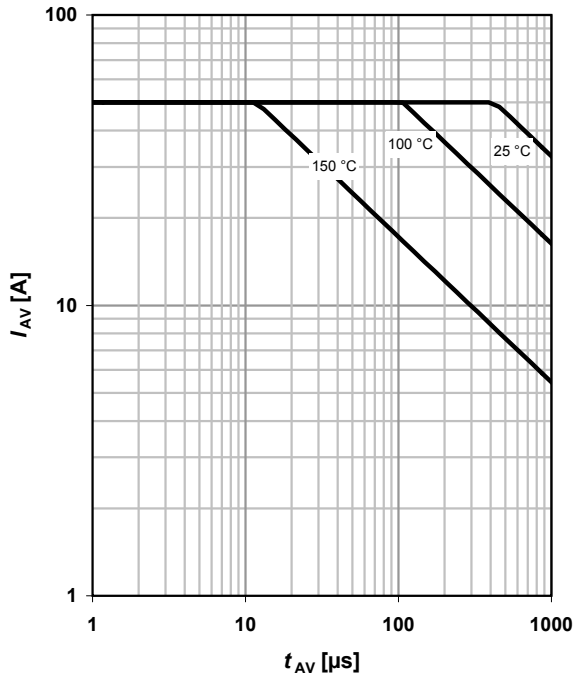
parameter:  $T_j$



**13 Avalanche characteristics**

$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$

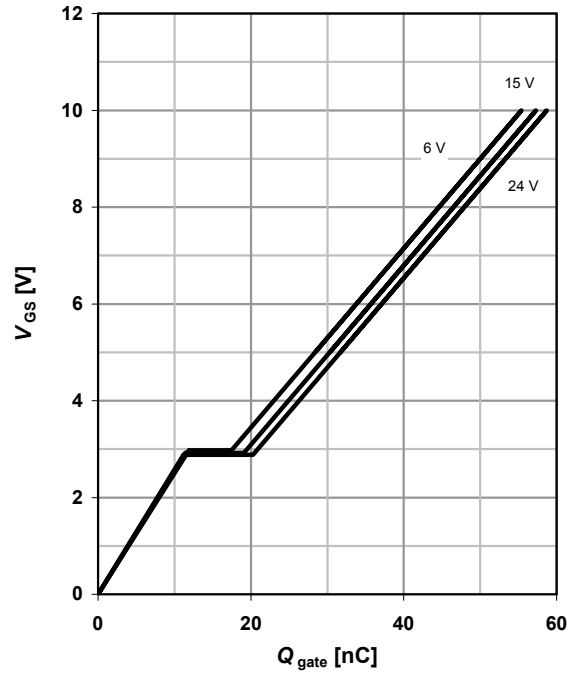
parameter:  $T_{j(start)}$



**14 Typ. gate charge**

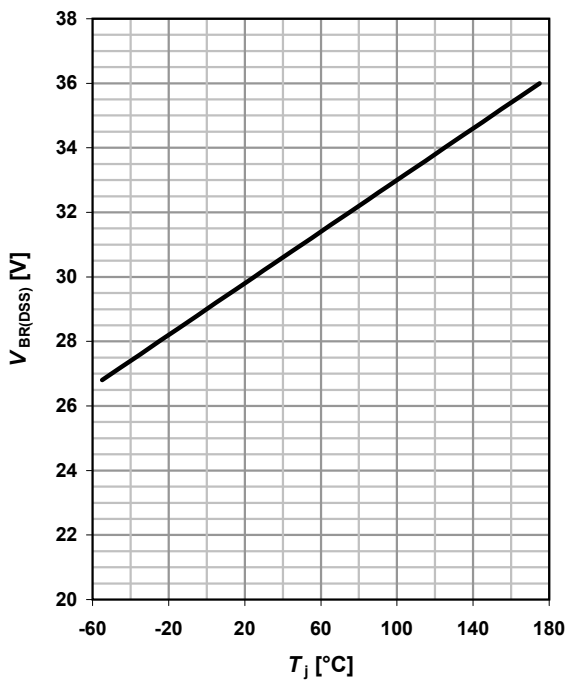
$V_{GS}=f(Q_{gate}); I_D=25 \text{ A pulsed}$

parameter:  $V_{DD}$

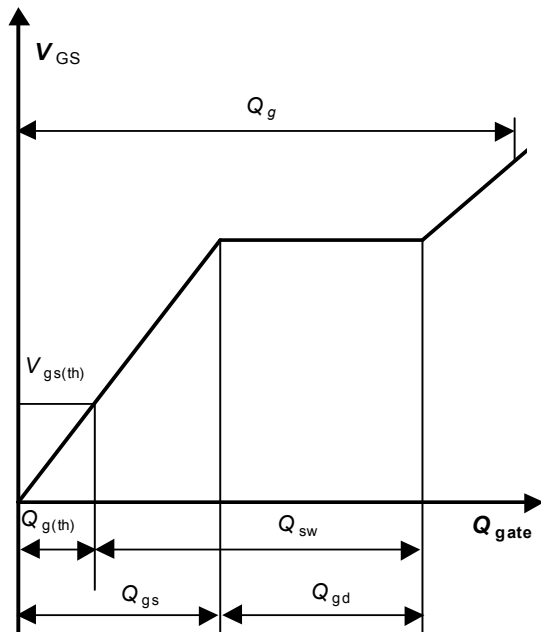


**15 Drain-source breakdown voltage**

$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

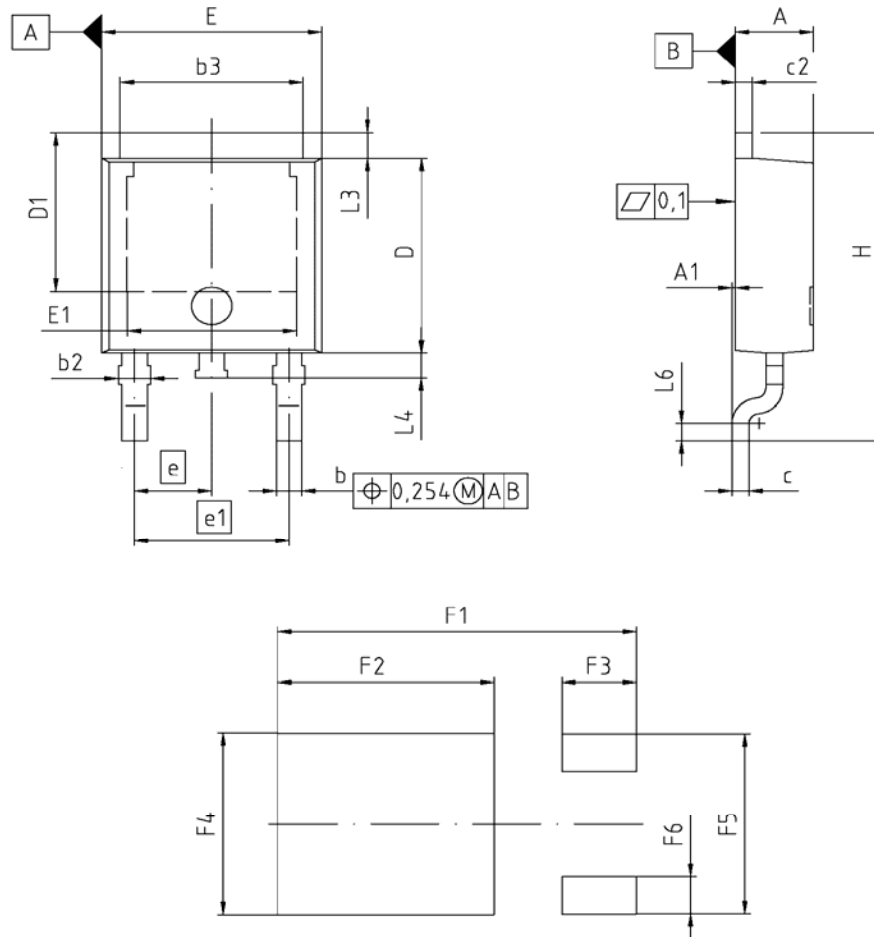


**16 Gate charge waveforms**



## Package Outline

## PG-TO252-3-11



| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 2.159       | 2.413  | 0.085  | 0.095 |
| A1  | 0.000       | 0.150  | 0.000  | 0.006 |
| b   | 0.635       | 0.889  | 0.025  | 0.035 |
| b2  | 0.650       | 1.150  | 0.026  | 0.045 |
| b3  | 5.004       | 5.500  | 0.197  | 0.217 |
| c   | 0.457       | 0.580  | 0.018  | 0.023 |
| c2  | 0.460       | 0.980  | 0.018  | 0.039 |
| D   | 5.969       | 6.223  | 0.235  | 0.245 |
| D1  | 5.020       | 5.842  | 0.198  | 0.230 |
| E   | 6.400       | 6.731  | 0.252  | 0.265 |
| E1  | 4.850       | 5.207  | 0.191  | 0.205 |
| e   | 2.286       |        | 0.090  |       |
| e1  | 4.572       |        | 0.180  |       |
| N   | 3           |        | 3      |       |
| H   | 9.400       | 10.480 | 0.370  | 0.413 |
| L3  | 0.900       | 1.143  | 0.035  | 0.045 |
| L4  | 0.584       | 0.950  | 0.023  | 0.037 |
| L6  | 0.510       | 0.686  | 0.020  | 0.027 |
| F1  | 10.500      | 10.700 | 0.413  | 0.421 |
| F2  | 6.300       | 6.500  | 0.248  | 0.256 |
| F3  | 2.100       | 2.300  | 0.083  | 0.091 |
| F4  | 5.700       | 5.900  | 0.224  | 0.232 |
| F5  | 5.660       | 5.860  | 0.222  | 0.231 |
| F6  | 1.100       | 1.300  | 0.043  | 0.051 |

**REFERENCE**  
JEDEC TO252

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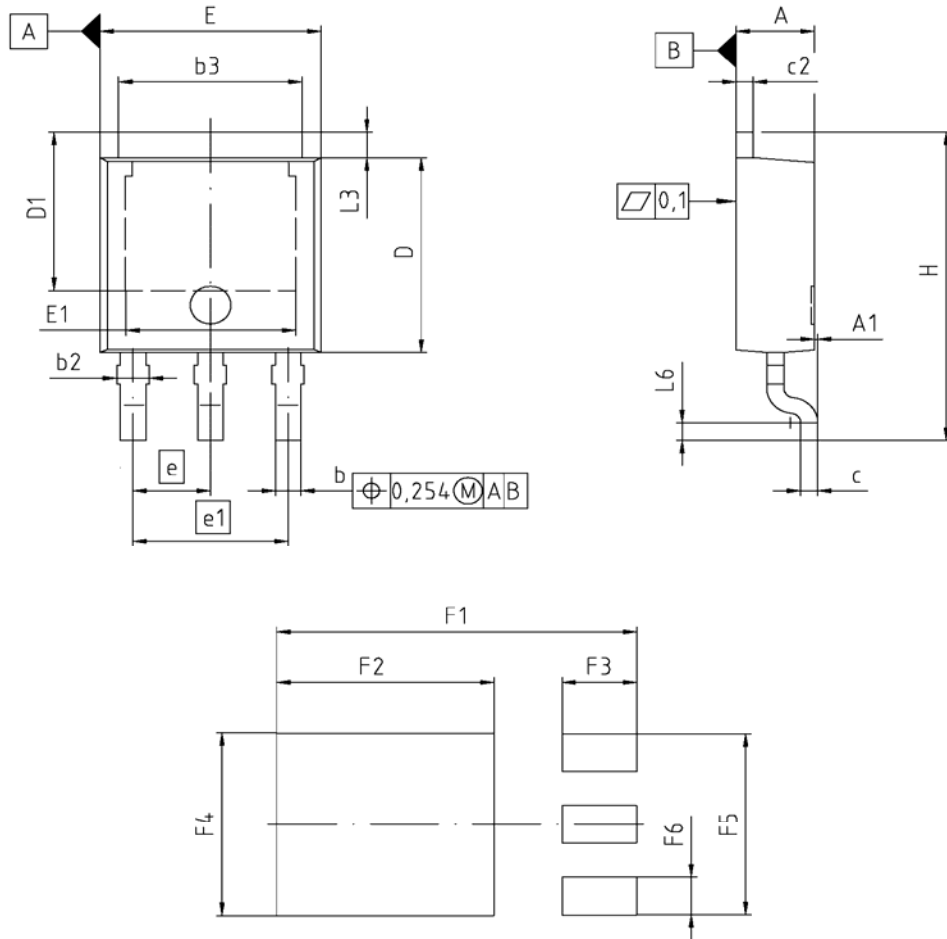
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Package Outline

PG-TO252-3-23



| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 2.159       | 2.413  | 0.085  | 0.095 |
| A1  | 0.000       | 0.150  | 0.000  | 0.006 |
| b   | 0.635       | 0.889  | 0.025  | 0.035 |
| b2  | 0.650       | 1.150  | 0.026  | 0.045 |
| b3  | 5.004       | 5.500  | 0.197  | 0.217 |
| c   | 0.457       | 0.580  | 0.018  | 0.023 |
| c2  | 0.460       | 0.980  | 0.018  | 0.039 |
| D   | 5.969       | 6.223  | 0.235  | 0.245 |
| D1  | 5.020       | 5.842  | 0.198  | 0.230 |
| E   | 6.400       | 6.731  | 0.252  | 0.265 |
| E1  | 4.850       | 5.207  | 0.191  | 0.205 |
| e   | 2.286       |        | 0.090  |       |
| e1  | 4.572       |        | 0.180  |       |
| N   | 3           |        | 3      |       |
| H   | 9.400       | 10.480 | 0.370  | 0.413 |
| L3  | 0.900       | 1.143  | 0.035  | 0.045 |
| L4  | 0.584       | 0.950  | 0.023  | 0.037 |
| L6  | 0.510       | 0.686  | 0.020  | 0.027 |
| F1  | 10.500      | 10.700 | 0.413  | 0.421 |
| F2  | 6.300       | 6.500  | 0.248  | 0.256 |
| F3  | 2.100       | 2.300  | 0.083  | 0.091 |
| F4  | 5.700       | 5.900  | 0.224  | 0.232 |
| F5  | 5.660       | 5.860  | 0.222  | 0.231 |
| F6  | 1.100       | 1.300  | 0.043  | 0.051 |

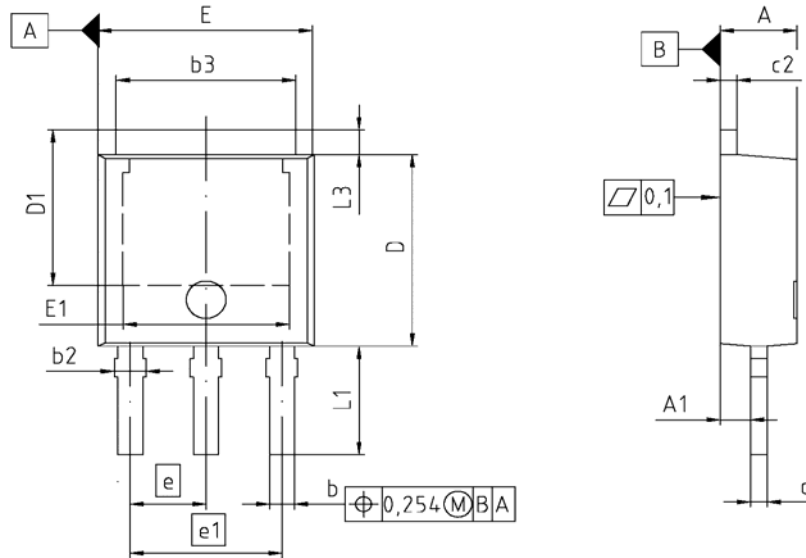
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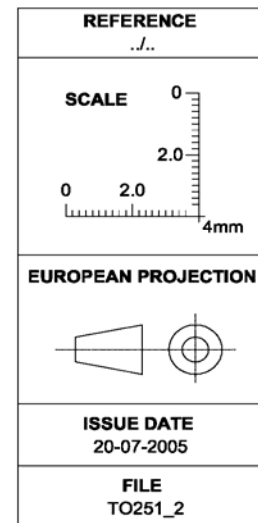
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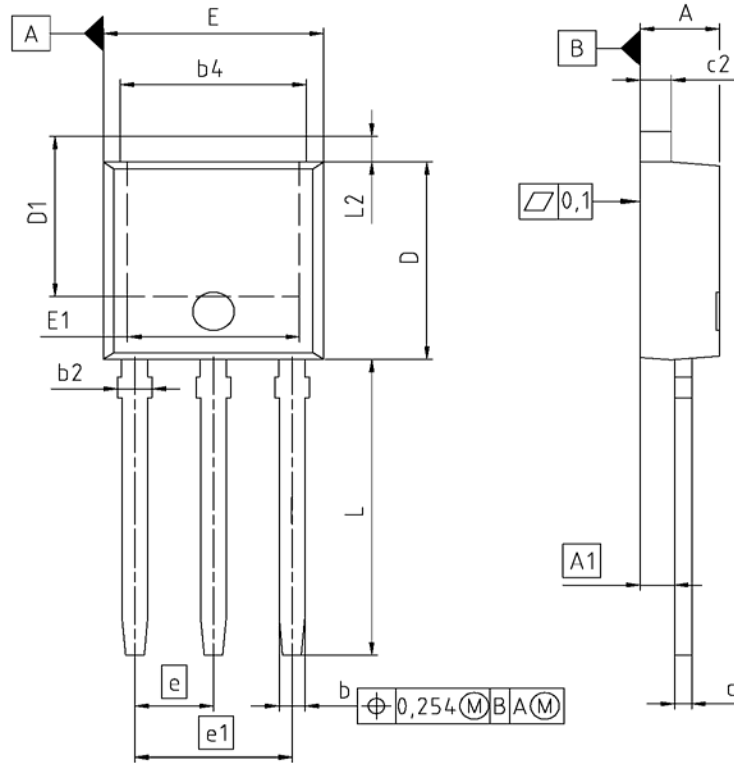


| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 2.184       | 2.388 | 0.086  | 0.094 |
| A1  | 0.000       | 0.150 | 0.000  | 0.006 |
| b   | 0.635       | 0.889 | 0.025  | 0.035 |
| b2  | 0.650       | 1.150 | 0.025  | 0.045 |
| b3  | 5.004       | 5.500 | 0.197  | 0.217 |
| c   | 0.460       | 0.580 | 0.018  | 0.023 |
| c2  | 0.460       | 0.980 | 0.018  | 0.039 |
| D   | 5.969       | 6.223 | 0.235  | 0.245 |
| D1  | 5.020       | 5.320 | 0.198  | 0.209 |
| E   | 6.400       | 6.731 | 0.252  | 0.265 |
| E1  | 4.900       | 5.100 | 0.193  | 0.201 |
| e   | 2.286       |       | 0.090  |       |
| e1  | 4.572       |       | 0.180  |       |
| N   | 3           |       | 3      |       |
| L1  | 3.400       | 3.600 | 0.134  | 0.142 |
| L3  | 0.900       | 1.118 | 0.035  | 0.044 |



Package Outline

PG-TO251-3-21



| DIM | MILLIMETERS |       | INCHES |       |
|-----|-------------|-------|--------|-------|
|     | MIN         | MAX   | MIN    | MAX   |
| A   | 2.159       | 2.413 | 0.085  | 0.095 |
| A1  | 0.900       | 1.118 | 0.035  | 0.044 |
| b   | 0.650       | 0.850 | 0.026  | 0.033 |
| b2  | 0.650       | 1.150 | 0.026  | 0.045 |
| b4  | 5.004       | 5.500 | 0.197  | 0.217 |
| c   | 0.457       | 0.580 | 0.018  | 0.023 |
| c2  | 0.737       | 0.980 | 0.029  | 0.039 |
| D   | 5.969       | 6.223 | 0.235  | 0.245 |
| D1  | 5.100       | 6.121 | 0.201  | 0.241 |
| E   | 6.400       | 6.731 | 0.252  | 0.265 |
| E1  | 4.850       | 5.207 | 0.191  | 0.205 |
| e   | 2.286       |       | 0.090  |       |
| e1  | 4.572       |       | 0.180  |       |
| N   | 3           |       | 3      |       |
| L   | 8.900       | 9.525 | 0.350  | 0.375 |
| L1  | 0.900       | 1.143 | 0.035  | 0.045 |

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**SCALE**

**EUROPEAN PROJECTION**

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